

TOSHIBA TRANSISTOR SILICON PNP TRIPLE DIFFUSED TYPE

2SA2034

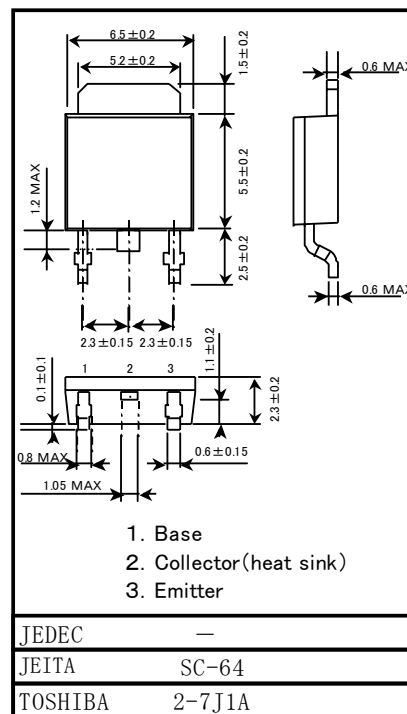
High Voltage Switching Applications

- High Voltage : $V_{CBO} = -400\text{ V}$
- High Speed : $t_f = 0.3\text{ }\mu\text{s (Max.) (}I_C = -1.0\text{A)}$

MAXIMUM RATINGS ($T_c = 25^\circ\text{C}$)

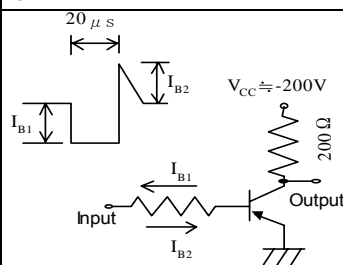
CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-400	V
Collector-Emitter Voltage	V_{CEO}	-400	V
Emitter-Base Voltage	V_{EBO}	-7	V
Collector Current	DC	I_C	A
	Pulse	I_{CP}	
Base Current	I_B	-1	A
Collector Power Dissipation	$T_a = 25^\circ\text{C}$	P_C	W
	$T_c = 25^\circ\text{C}$	15	
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55~150	$^\circ\text{C}$

Unit : mm

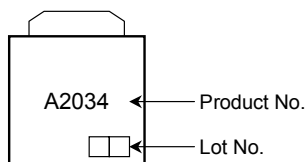


Weight : 0.36 g (Typ.)

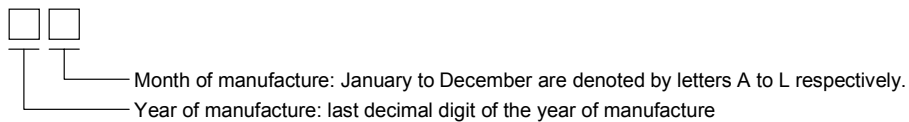
ELECTRICAL CHARACTERISTICS (T_c = 25°C)

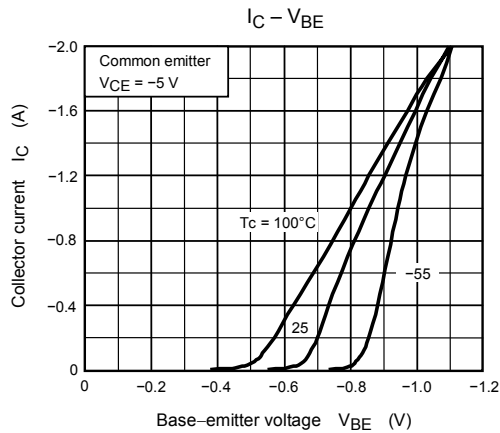
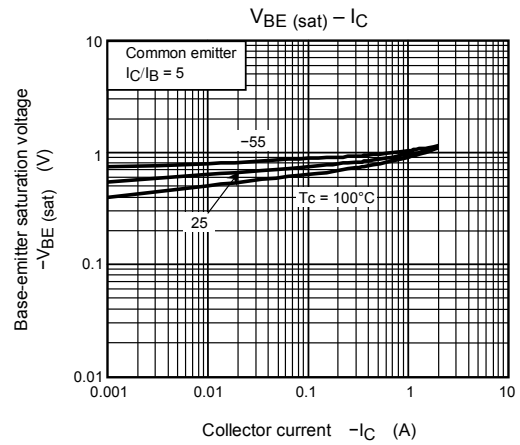
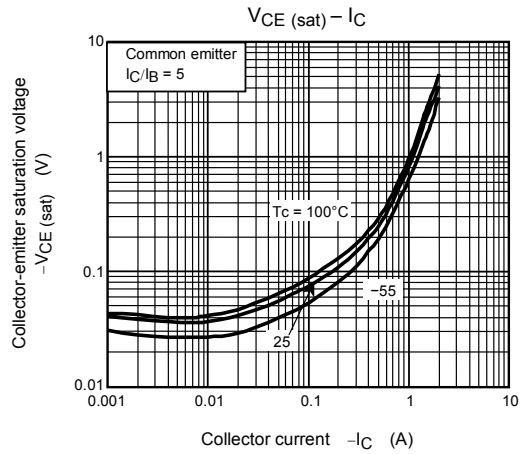
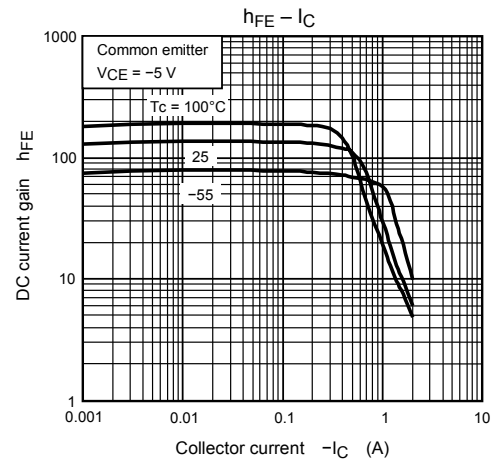
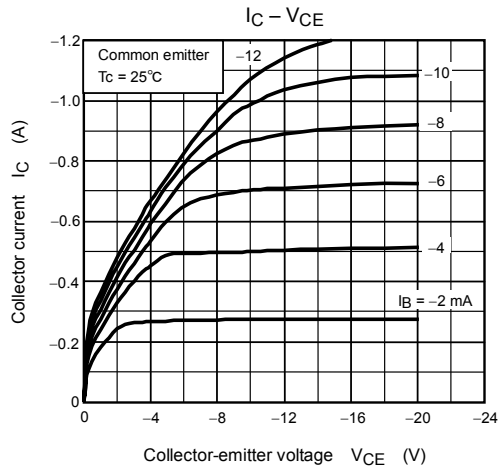
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN	TYP.	MAX	UNIT
Collector Cut-off Current		I _{CBO}	V _{CB} = -400 V, I _E = 0	—	—	-10	μA
Emitter Cut-off Current		I _{EBO}	V _{EB} = -7 V, I _C = 0	—	—	-1	μA
Collector - Emitter Breakdown Voltage		V _{(BR) CEO}	I _C = -10 mA, I _B = 0	-400	—	—	V
DC Current Gain		h _{FE} (1)	V _{CE} = -5 V, I _C = -1 mA	80	—	—	—
		h _{FE} (2)	V _{CE} = -5 V, I _C = -0.1 A	80	—	240	
Collector-Emitter Saturation Voltage		V _{CE (sat)}	I _C = -0.5 A, I _B = -0.1 A	—	—	-1.0	V
Base-Emitter Saturation Voltage		V _{BE (sat)}	I _C = -0.5 A, I _B = -0.1 A	—	—	-1.5	V
Switching Time	Rise Time	t _r	 <p>IB1 = -IB2 = -0.2A Duty cycle < 1%</p>	—	—	0.3	μs
	Storage time	t _{stg}		—	—	2.5	
	Fall time	t _f		—	—	0.3	

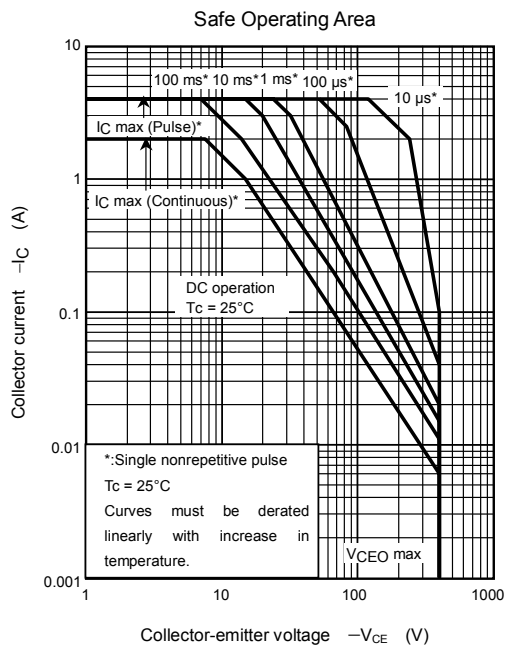
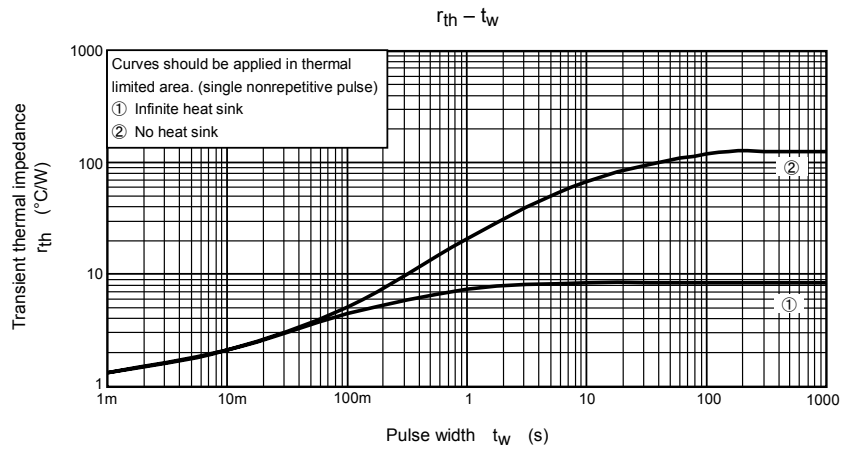
Marking



Explanation of Lot No.







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